

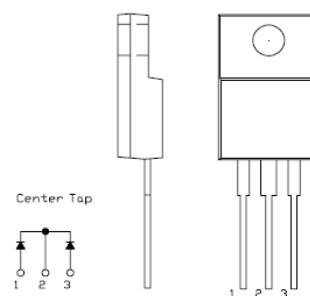
MBRF4060CT SCHOTTKY RECTIFIER

Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

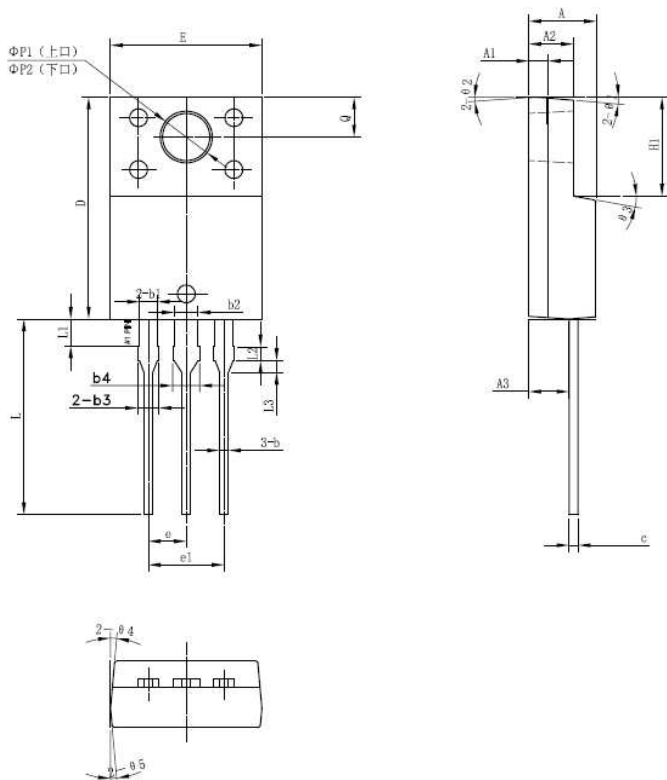
Features:

- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



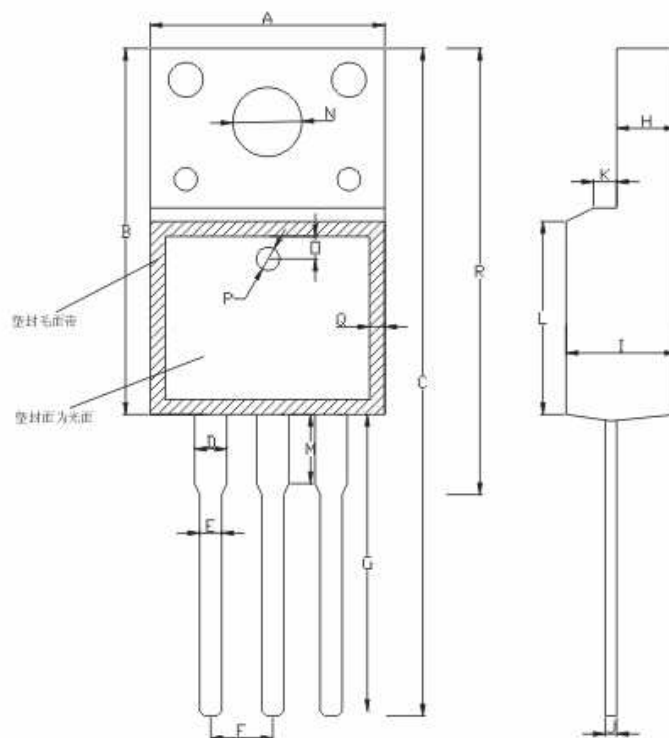
OUTLINE DRAWING

Mechanical Dimensions: In mm



SYMBOL	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.55	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

OPTION1(HD)

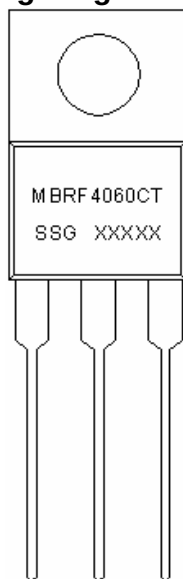


A:10.20 ± 0.50	B:15.90 ± 0.50	C:29.00 ± 1.00	D:1.24 ± 0.10
E:0.80 ± 0.10	F:2.54 ± 0.10	G:13.10 ± 1.0	H:2.55 ± 0.05
I:4.70 ± 0.05	J:0.50 ± 0.05	K:1.20 ± 0.20	L:8.00 ± 0.50
M:3.00 ± 0.50	N:3.20 ± 0.20	O:1.25 ± 0.05	P:1.5 ± 0.05
Q:1.0 ± 0.20	R:19.2 ± 1.0		

OPTION 2 (SR)

ITO-220AB

Marking Diagram:



Where XXXXX is YYWWL

MBR = Device Type
F = Package type
40 = Forward Current (40A)
60 = Reverse Voltage (60V)
CT = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBRF4060CT	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward Current	$I_{F(AV)}$	@ $T_C = 105^\circ\text{C}$, Rated V_R	40	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	400	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V _{F1}	@ 20A, Pulse, T _J = 25 °C	0.75	V
	V _{F2}	@ 20A, Pulse, T _J = 125 °C	0.65	V
Max. Reverse Current (per leg) *	I _{R1}	@V _R = rated V _R T _J = 25 °C	1	mA
	I _{R2}	@V _R = rated V _R T _J = 100°C	75	mA
	I _{R3}	@V _R = rated V _R T _J = 125°C	95	mA
Max. Junction Capacitance (per leg)	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	900	pF
Typical Series Inductance (per leg)	L _S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

* Pulse Width < 300μs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature Range	T _J	-	-55 to +150	°C
Storage Temperature Range	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	R _{θJC}	DC operation	1.5	°C/W
Maximum Thermal Resistance, Junction to Case(Per package)	R _{θJC}	DC operation	50	°C/W
Maximum Thermal Resistance, Case to Heat Sink	R _{θCS}	Mounting surface, smooth and greased (only for TO-220)	0.50	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

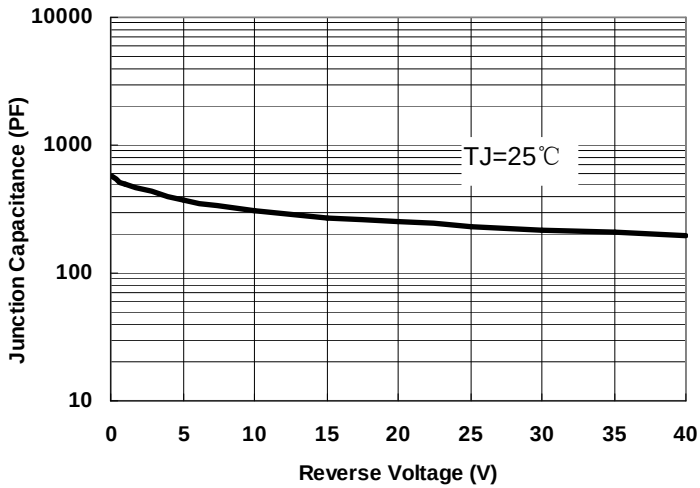


Fig.1-Typical Junction Capacitance

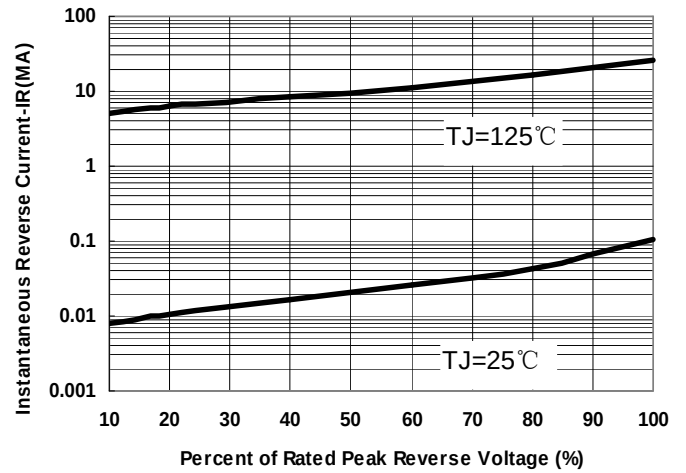


Fig.2-Typical Reverse Characteristics

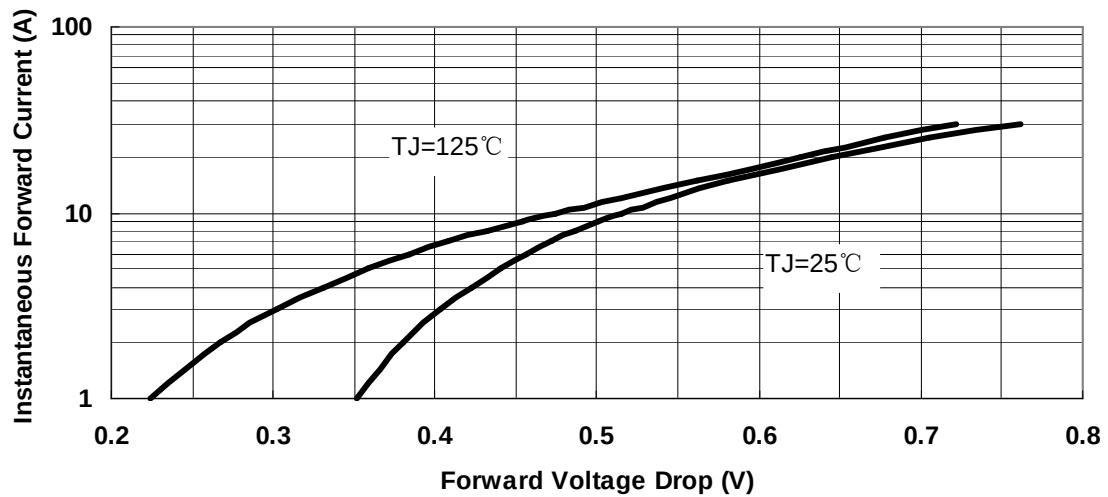


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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